

# PROCESS CP245

## Power Transistor

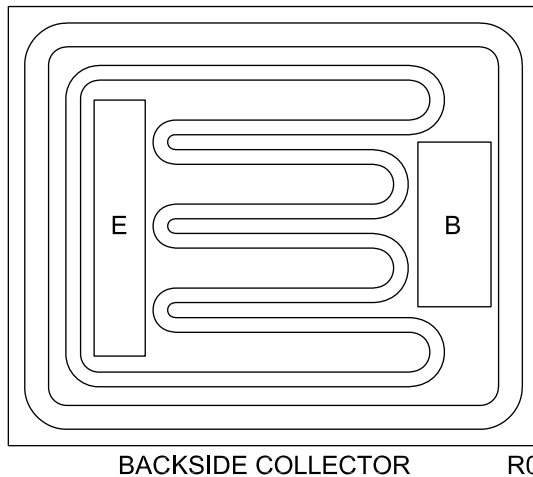
[查询"CP245"供应商](#)  
NPN, 6.0A Power Transistor Chip

**Central**<sup>TM</sup>  
Semiconductor Corp.

### PROCESS DETAILS

|                          |                        |
|--------------------------|------------------------|
| Process                  | MULTIEPITAXIAL MESA    |
| Die Size                 | 120 x 145 MILS         |
| Die Thickness            | 13 MILS                |
| Base Bonding Pad Area    | 20 x 45 MILS           |
| Emitter Bonding Pad Area | 14 x 70 MILS           |
| Top Side Metalization    | Al - 50,000Å           |
| Back Side Metalization   | Cr / Ni / Ag - 10,000Å |

### GEOMETRY



### GROSS DIE PER 4 INCH WAFER

640

### PRINCIPAL DEVICE TYPES

MJE15030

145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
[www.centralsemi.com](http://www.centralsemi.com)

R0 (4- April 2005)